

Chi-Woo Lee

List of Publications by Year in descending order

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18
papers

4,648
citations

567281

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888059

17
g-index

18
all docs

18
docs citations

18
times ranked

1895
citing authors

#	ARTICLE	IF	CITATIONS
1	Low-frequency noise in junctionless multigate transistors. Applied Physics Letters, 2011, 98, .	3.3	52
2	Junctionless Multiple-Gate Transistors for Analog Applications. IEEE Transactions on Electron Devices, 2011, 58, 2511-2519.	3.0	234
3	Investigation of high-performance sub-50nm junctionless nanowire transistors. Microelectronics Reliability, 2011, 51, 1166-1171.	1.7	32
4	Performance estimation of junctionless multigate transistors. Solid-State Electronics, 2010, 54, 97-103.	1.4	487
5	Nanowire transistors without junctions. Nature Nanotechnology, 2010, 5, 225-229.	31.5	1,993
6	Low-temperature conductance oscillations in junctionless nanowire transistors. Applied Physics Letters, 2010, 97, 172101.	3.3	32
7	Reduced electric field in junctionless transistors. Applied Physics Letters, 2010, 96, 073510.	3.3	269
8	Mobility improvement in nanowire junctionless transistors by uniaxial strain. Applied Physics Letters, 2010, 97, .	3.3	38
9	Low subthreshold slope in junctionless multigate transistors. Applied Physics Letters, 2010, 96, .	3.3	195
10	High-Temperature Performance of Silicon Junctionless MOSFETs. IEEE Transactions on Electron Devices, 2010, 57, 620-625.	3.0	359
11	Nanowire zero-capacitor DRAM transistors with and without junctions. , 2010, , .		17
12	Comparison of different surface orientation in narrow fin MuGFETs. Microelectronic Engineering, 2009, 86, 2381-2384.	2.4	5
13	Analytical model for the high-temperature behaviour of the subthreshold slope in MuGFETs. Microelectronic Engineering, 2009, 86, 2067-2071.	2.4	3
14	Junctionless multigate field-effect transistor. Applied Physics Letters, 2009, 94, .	3.3	768
15	Comparison of contact resistance between accumulation-mode and inversion-mode multigate FETs. Solid-State Electronics, 2008, 52, 1815-1820.	1.4	16
16	Sensitivity of trigate MOSFETs to random dopant induced threshold voltage fluctuations. Solid-State Electronics, 2008, 52, 1872-1876.	1.4	32
17	Drain Breakdown Voltage in MuGFETs: Influence of Physical Parameters. IEEE Transactions on Electron Devices, 2008, 55, 3503-3506.	3.0	16
18	Device design guidelines for nano-scale MuGFETs. Solid-State Electronics, 2007, 51, 505-510.	1.4	100